L Number	Hits	Search Text	DB	Time stamp
1	0	174/141.ccls.	USPAT	2004/04/26 14:27
	10	174/141.ccis. 174/141c.ccis.	USPAT	2004/04/26 14:28
2				
3	222	174/149r.ccls.	USPAT	2004/04/26 14:28
4	232	174/141c.ccls. 174/149r.ccls.	USPAT	2004/04/26 14:28
5	0	(174/141c.ccls. 174/149r.ccls.) and ("low k" "low-k")	USPAT	2004/04/26 14:29
6	2	(174/141c.ccls. 174/149r.ccls.) and carbon	USPAT	2004/04/26 14:29
7	0	(174/141c.ccls. 174/149r.ccls.) and "silicon oxide"	USPAT	2004/04/26 14:29
-	3908	"integrated circuit" and photodiode	USPAT;	2003/01/14 13:29
			EPO; JPO	
-	9061	photo adj diode	USPAT;	2003/01/13 15:28
			EPO; JPO	
-	1030	"integrated circuit" and (photo adj diode)	USPAT;	2003/01/13 15:29
			EPO; JPO	
] -	4304	("integrated circuit" and (photo adj diode)) or ("integrated	USPAT	2003/01/13 15:29
1		circuit" and photodiode)		
-	338	(("integrated circuit" and (photo adj diode)) or ("integrated	USPAT	2003/01/13 15:30
		circuit" and photodiode)) and "p-n"		
-	164	((("integrated circuit" and (photo adj diode)) or ("integrated	USPAT	2003/01/13 15:43
		circuit" and photodiode)) and "p-n") and (capacitor		
		capacitive)		
_	ol	"integrated circuit" and 5307169.pn.	USPAT;	2003/01/13 15:45
		• • • • • • • • • • • • • • • • • • •	EPO; JPO	
_	1	5307169.pn.	USPAT;	2003/01/13 15:45
	*		EPO; JPO	, , == : , =
_	0	5307169.pn. and "integrated circuit"	USPAT;	2003/01/13 15:45
		soor tos.pri. and integrated and all	EPO; JPO	
_	1	6207587.pn.	USPAT	2003/01/20 17:51
l <u>-</u>	3053	information adj processing adj system	USPAT	2003/01/20 17:51
	422	(information adj processing adj system) and "integrated	USPAT	2003/01/20 17:52
i -	. '22	circuit"		
-	35	((information adj processing adj system) and "integrated	USPAT	2003/01/20 17:52
	33	circuit") and ("photo gate" "photo diode" photodiode)	00.7	
_	1962	"low k"	USPAT;	2003/01/23 15:49
-	1902	IOW K	EPO; JPO	2000,02,20 221.0
	244	 "low k" and void	USPAT;	2003/01/23 16:01
-	277	low k and void	EPO; JPO	2000,02,20 20102
1_	1310	"low k" and oxide	USPAT;	2003/01/23 16:02
	1510	IOW R dild Oxide	EPO; JPO	2000,00,00
	1222	("low k" and oxide) and (metal conductive lines)	USPAT;	2003/01/23 16:02
-	1222	l low k and oxide) and (metal conductive intes)	EPO; JPO	2000,02,20 20.02
	1021	(("low k" and oxide) and (metal conductive lines)) not ("low	USPAT;	2003/01/23 16:18
1	1021	((low k and oxide) and (metal conductive lines)) not (low k and void)	EPO; JPO	
	30	breadloaf and semiconductor	USPAT;	2003/01/23 17:11
	30	bicadioal and Scilliconductor	EPO; JPO	2303,01,23 17.11
	4	("5708303" "5818111" "5821621" "5302233").pn.	USPAT;	2003/01/23 17:21
	"	(3700303 3010111 3021021 3302233).μπ.	EPO; JPO	2000,01,20 17.21
1	0	(("5708303" "5818111" "5821621" "5302233").pn.) and	USPAT	2003/01/23 17:14
-		((5708303 5818111 5821821 5302233).pn.) and carbon	03, 7,	2005,01,25 17.14
	30		USPAT	2003/01/23 17:14
-	28	hsq near carbon	USPAT;	2003/01/23 17:14
-	0	"5821621".pn. and void	EPO; JPO	2003/01/23 17.21
] _	5931631 an	USPAT	2003/06/17 17:01
-	1	5821621.pn.	USPAT	2003/06/17 17:01
-	1	5821621.pn. and "20"	USPAT	2003/06/17 17:01 2004/03/23 13:00
-	1	5281621.pn.		
1-	0	5281621.	USPAT	2004/03/23 13:00
1 -	1	5281621.pn.	USPAT	2004/03/23 13:01
-	1	5821621.pn.	USPAT	2004/03/23 13:01
1 -	718	438/787.ccls. 438/789.ccls.	USPAT	2004/03/29 15:16
-	2381830		USPAT	2004/03/29 15:17
-	620	(void adj3 free) (voidless) (without with3 void\$) and	USPAT	2004/03/29 15:18
		(438/787.ccls. 438/789.ccls.)	LICEAT	2004/02/20 17 17
-	17896	low adj2 k) (low adj2 dielectric	USPAT	2004/03/29 15:18

Search History 4/26/04 2:29:19 PM Page 1

-	17896	low adj2 k) (low adj2 dielectric) ("low-k dielectric") ("low k dielectric"	USPAT	2004/03/29 15:19
-	193	((void adj3 free) (voidless) (without with3 void\$) and (438/787.ccls. 438/789.ccls.)) and (low adj2 k) (low adj2	USPAT	2004/03/29 15:29
		dielectric) ("low-k dielectric") ("low k dielectric")		
-	121	(((void adj3 free) (voidless) (without with3 void\$) and	USPAT	2004/03/29 15:29
		(438/787.ccls. 438/789.ccls.)) and (low adj2 k) (low adj2		
		dielectric) ("low-k dielectric") ("low k dielectric")) and (cmp		
		planariz\$5)		
-	422	438/789.ccls. 438/790.ccls.	USPAT	2004/04/16 11:25
-	10424	"void-free" "without voids" (void near2 free) (without near2	USPAT	2004/04/16 11:26
		void\$1) (no adj2 void\$1)	LICDAT	2004/04/16 11:27
-	57	("void-free" "without voids" (void near2 free) (without near2 void\$1) (no adj2 void\$1)) and (438/789.ccls. 438/790.ccls.)	USPAT	2004/04/16 11:27
	2738	"low k" "low-k" "low k dielectric"	USPAT	2004/04/16 11:27
1	46582	(carbon near2 doped) with5 "silicon oxide"	USPAT	2004/04/16 11:29
	915	((carbon near2 doped) with5 "silicon oxide") and	USPAT	2004/04/16 11:28
	713	("void-free" "without voids" (void near2 free) (without near2	00,711	200 1, 0 1, 20 22120
		void\$1) (no adj2 void\$1))		
-	1043	((carbon near2 doped) with5 "silicon oxide") and ("low k"	USPAT	2004/04/16 11:28
		"low-k" "low k dielectric")		
-	38	((carbon near2 doped) with5 "silicon oxide") and	USPAT	2004/04/16 11:28
		(("void-free" "without voids" (void near2 free) (without		
		near2 void\$1) (no adj2 void\$1)) and (438/789.ccls.		
		438/790.ccls.))	LICDAT	2004/04/16 11:20
-	369	"carbon-doped silicon" (carbon near2 dop\$3 near2 (silicon	USPAT	2004/04/16 11:30
	21	oxide)) ("void-free" "without voids" (void near2 free) (without near2	USPAT	2004/04/16 11:41
-	21	void\$1) (no adj2 void\$1)) and ("carbon-doped silicon"	05171	200 1/0 1/10 11: 11
		(carbon near2 dop\$3 near2 (silicon oxide)))		
-	1952	438/624.ccls. 438/763.ccls. 438/631.ccls.	USPAT	2004/04/16 11:41
_	268	"black diamond"	USPAT	2004/04/16 11:42
-	10	"black diamond" and ("void-free" "without voids" (void near2	USPAT	2004/04/16 11:42
		free) (without near2 void\$1) (no adj2 void\$1))		
-	658	252/1.ccls.	USPAT	2004/04/16 11:43
-	2933	(438/789.ccls. 438/790.ccls.) 252/1.ccls. (438/624.ccls.	USPAT	2004/04/16 11:43
	1124	438/763.ccls. 438/631.ccls.)	USPAT	2004/04/16 11:43
-	1124	((438/789.ccls, 438/790.ccls,) 252/1.ccls, (438/624.ccls, 438/763.ccls, 438/631.ccls,)) and ((carbon near2 doped)	USPAT	2007/07/10 11.15
		with5 "silicon oxide")		
<u>-</u>	47	(((438/789.ccls. 438/790.ccls.) 252/1.ccls. (438/624.ccls.	USPAT	2004/04/16 12:19
	"	438/763.ccls. 438/631.ccls.)) and ((carbon near2 doped)		
		with5 "silicon oxide")) and ("carbon-doped silicon" (carbon		
		near2 dop\$3 near2 (silicon oxide)))		
-	775	(carbonaceous adj2 (silicon oxide)) SiOC	USPAT;	2004/04/16 12:19
			US-PGPUB;	
			EPO; JPO	2004/04/16 12:22
-	221	trikon	USPAT;	2004/04/16 12:22
			US-PGPUB; EPO; JPO	
	152	trikon and (speed deposition rate)	USPAT;	2004/04/16 12:22
-	152	dikon and (speed deposition rate)	US-PGPUB;	2001/01/1012.22
			EPO; JPO	
_	80	trikon and (speed "deposition rate")	USPAT;	2004/04/16 13:12
		,	US-PGPUB;	
			EPO; JPO	
-	3	((carbonaceous adj2 (silicon oxide)) SiOC) and (trikon and	USPAT;	2004/04/16 12:24
		(speed "deposition rate"))	US-PGPUB;	
		10 / 111 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	EPO; JPO	2004/04/46 42 54
-	36	((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon	USPAT;	2004/04/16 12:24
		doped" "carbon-doped")	US-PGPUB; EPO; JPO	
	<u> </u>		1 FLO' 250	

-	39	(((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon	USPAT;	2004/04/16 12:27
		doped" "carbon-doped")) (((carbonaceous adj2 (silicon	US-PGPUB;	
		oxide)) SiOC) and (trikon and (speed "deposition rate")))	EPO; JPO	
-	4	((((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon	USPAT;	2004/04/16 12:25
		doped" "carbon-doped")) (((carbonaceous adj2 (silicon	US-PGPUB;	
		oxide)) SiOC) and (trikon and (speed "deposition rate"))))	EPO; JPO	
		and trikon		
-	6	((((carbonaceous adj2 (silicon oxide)) SiOC) and ("carbon	USPAT;	2004/04/16 12:27
		doped" "carbon-doped")) (((carbonaceous adj2 (silicon	US-PGPUB;	
		oxide)) SiOC) and (trikon and (speed "deposition rate"))))	EPO; JPO	
		and ("deposition rate")		
-	520521	"Pursuing the Perfect Low-k Dielectric"	USPAT;	2004/04/16 13:09
			DERWENT;	
			IBM_TDB	
-	308324	"Pursuing the Perfect Low-k Dielectric".ti.	USPAT;	2004/04/16 13:10
			DERWENT;	
			IBM_TDB	
-	73421	"Pursuing the Perfect Low-k Dielectric".ti.	DERWENT;	2004/04/16 13:10
			IBM_TDB	
-	0	"pursuing the perfect low-k dielectric"	DERWENT;	2004/04/16 13:11
			IBM_TDB	
-	0	"pursuing the perfect low-k dielectric"	USPAT;	2004/04/16 13:11
			DERWENT;	
			IBM_TDB	
-	43	trikon and (speed "deposition rate") and peters	USPAT;	2004/04/16 13:19
			US-PGPUB;	
			EPO; JPO	
-	0	wo/9747038	USPAT;	2004/04/16 13:19
			US-PGPUB;	
			EPO; JPO	